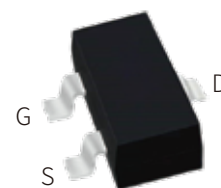


FEATURES

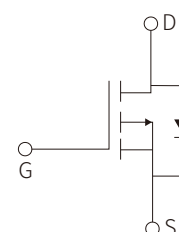
- | High Density Cell Design For Low $R_{DS(On)}$
- | Voltage Controlled Small Signal Switch
- | Rugged and Reliable
- | High Saturation Current Capability
- | Lead free product is acquired
- | Meet AEC-Q101 Requirements



SOT-23



Marking



Schematic Symbol

APPLICATION

- | Direct logic-level interface: TTL/CMOS
- | Drivers: relays, solenoids, lamps
- | hammers, display, memories, etc.
- | Battery operated systems
- | Solid-state relays

APPROVALS

RoHS	Compliance with 2011/65/EU
HF	Compliance with IEC61249-2-21:2003

ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Maximum Drain Current - Continuous	I_D	-3	A
Gate-Source Voltage	V_{GS}	± 12	V
Maximum Power Dissipation	P_D	1	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	125	$^{\circ}\text{C/W}$
Junction Temperature	T_J	-55 to 150	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 to 150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
Drain-source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			-1	μA
Gate-body leakage current	I_{GSSL}	$V_{GS}=\pm 12V, V_{DS}=0V$			± 100	nA
On Characteristics ^(Note 3)						
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.62	-1.0	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-2.0A$		61	77	m Ω
		$V_{GS}=-2.5V, I_D=-1.0A$		82	102	m Ω
Dynamic Characteristics ^(Note4)						
Input capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V, f=1MHz$		405		pF
Output capacitance	C_{oss}			75		pF
Reverse transfer capacitance	C_{rss}			55		pF
Switching Characteristics ^(Note4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=-1A$ $V_{GS}=-4.5V, R_{GEN}=10\Omega$		11		nS
Turn-on Rise Time	t_r			35		nS
Turn-Off Delay Time	$t_{d(off)}$			30		nS
Turn-Off Fall Time	t_f			10		nS
Total Gate Charge	Q_g	$V_{DS}=-10V, I_D=-3A$		3.3	12	nC
Gate-Source Charge	Q_{gs}			0.7		nC
Gate-Drain Charge	Q_{gd}			1.3		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=1.3A$			-1.2	V
Diode Forward Current ^(Note 2)	I_S				-3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

PARAMETER CHARACTERISTIC CURVE

Figure 1: Power Dissipation

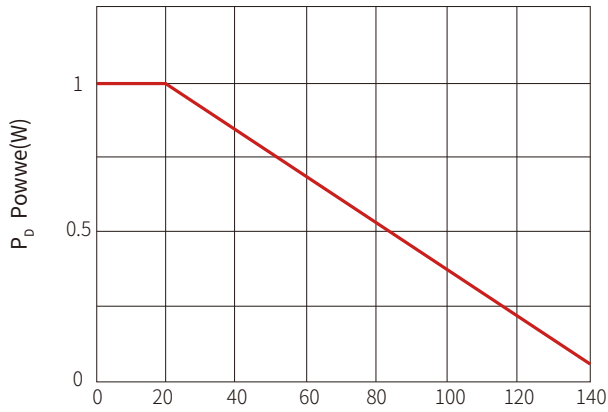


Figure 2: Drain Current

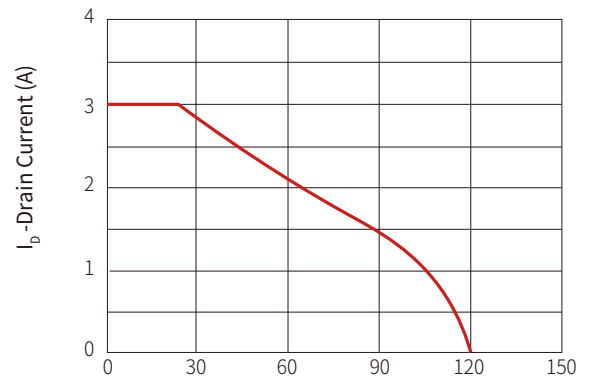


Figure 3: Output Characteristics

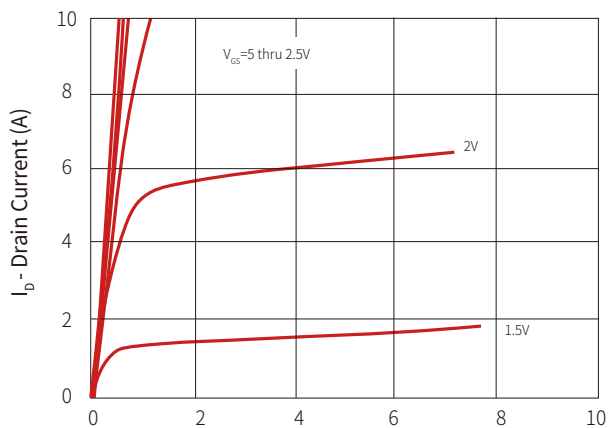


Figure 4: Drain-Source On-Resistance

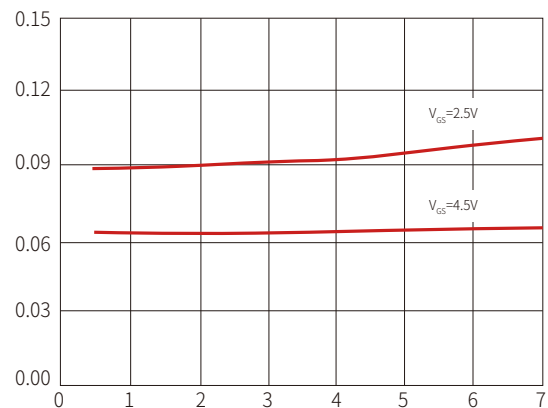


Figure 5: Transfer Characteristics

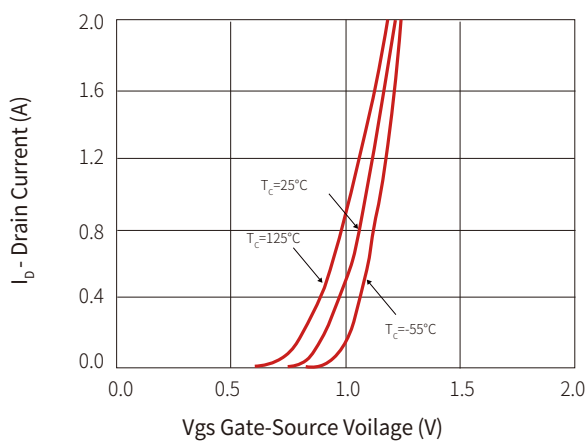


Figure 6: Drain-Source On-Resistance

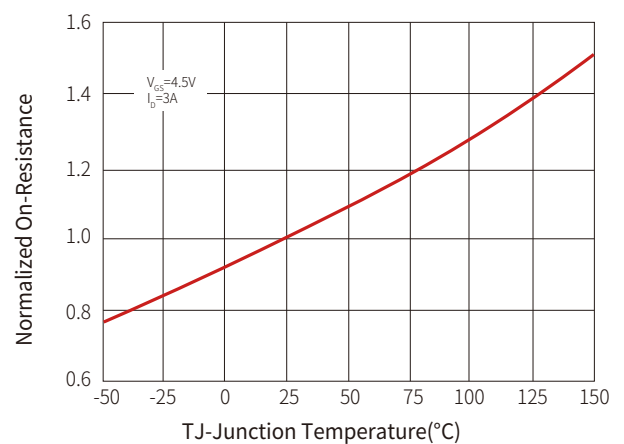
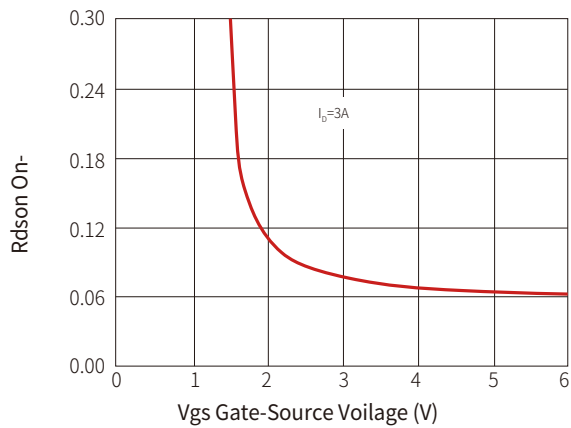
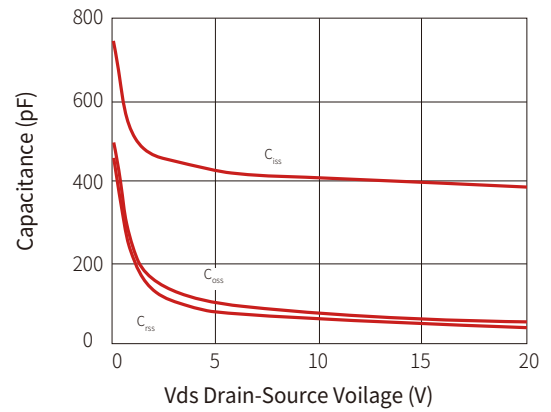
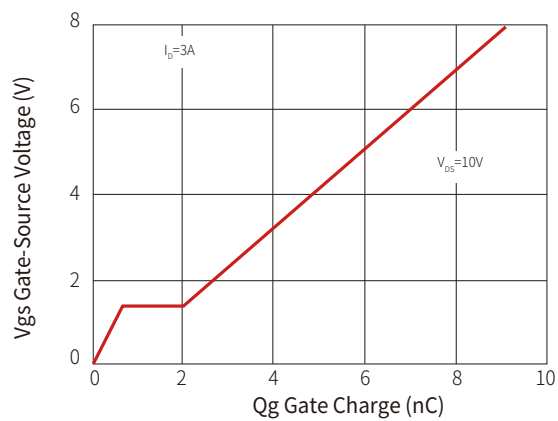
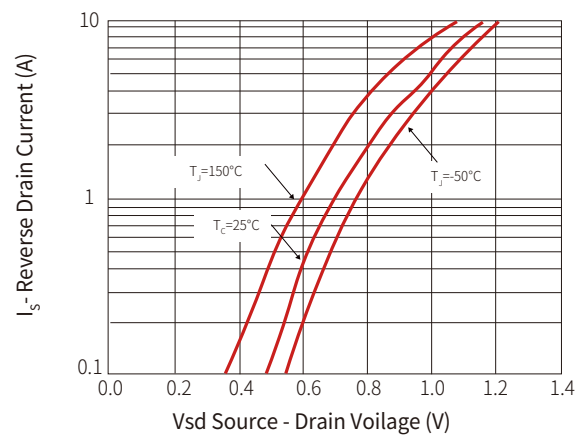
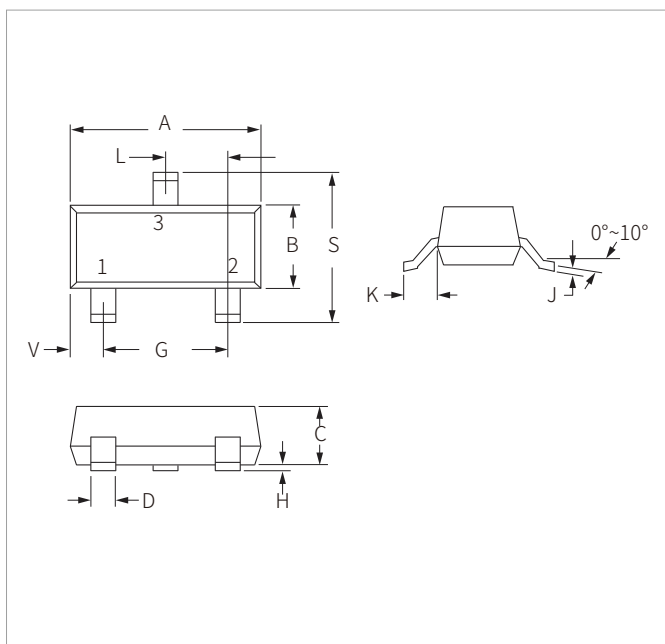


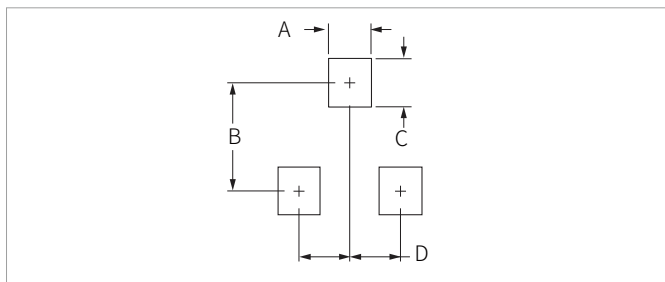
Figure 7: Rdson vs Vgs

Figure 8: Capacitance vs Vds

Figure 9: Gate Charge

Figure 10: Source- Drain Diode Forward


SOT-23 PACKAGE INFORMATION



Ref.	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.80	3.05	0.110	0.120
B	1.20	1.40	0.047	0.055
C	0.90	1.15	0.035	0.045
D	0.37	0.50	0.015	0.020
G	1.75	2.05	0.069	0.081
H	0.01	0.100	0.001	0.004
J	0.085	0.180	0.003	0.007
K	0.35	0.69	0.014	0.029
L	0.89	1.02	0.035	0.040
S	2.10	2.65	0.083	0.104
V	0.45	0.60	0.018	0.024

RECOMMENDED PAD LAYOUT DIMENSIONS



Ref.	Millimeters		Inches	
	Min	Max	Min	Max
A	0.71	0.97	0.028	0.038
B	1.88	2.13	0.074	0.084
C	0.71	0.97	0.028	0.038
D	0.81	1.07	0.032	0.042

ORDERING INFORMATION

Part Number	Component Package	QTY/Reel	Reel Size
SPM2301SQ	SOT-23	3000PCS	7"

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